

YJ Planar Schottky Barrier Diode Die Specification

40V 0.5A, 25mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB025L040AS-180A

Main Products Characterstics

- Average forward current: $I_F(AV) = 0.5\text{ A}$
- Maximum operating junction temperature: $T_j = 125\text{ }^{\circ}\text{C}$
- Top metal: AL

Maximum Ratings

Static Electrical Characteristics (Ta = 25°C)

$I_F = 0.5\text{ A}$
Pulse Test: $t_p = 300\text{ }\mu\text{s}$, $\delta \leq 2\%$

Device Schematics and Outline Drawing

Die Thickness *
Die Size **
Top Metal Pad
Active Area
Top Metal
Back Metal
Note: 1 * : Also can offer device with 10.5 mils thickness
2 **: Cutting street width is around 1.5 mils

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.
does not guarantee device performance after assembly.

Recommended Storage Environment:
Store in original container, in dessicated nitrogen, with no contamination.